

1. Scope :

This specification applies to silicon non-zero-crossing phototriac chips,
Device No. ST-1127S

2. Structure :

- 2-1. Planar type .
- 2-2. Electrodes :aluminum alloy

3. Size :

- 3-1. Chip size : 40 mils × 40 mils (1.016 mm ×1.016mm).
- 3-2. Chip thickness : 12±1.5 mil (0.305± 0.038 mm).
- 3-3. Pad area : 6 mil dia (0.152 mm dia).
- 3-4. Pattern drawing : refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Peak blocking Current	I_{DRM}	$V_{DRM}=800V$			500	nA
Peak on-state voltage	V_{TM}	$I_{TM}=100mA$		1.6	2.2	V
Critical rate of Rise voltage	dv/dt		1000			V/ μ S
Holding current	I_H			200		μ A

